

## Product Summary

Device	BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
Q1	20V	0.4Ω @ V <sub>GS</sub> = 4.5V	870mA
		0.5Ω @ V <sub>GS</sub> = 2.5V	780mA
		0.7Ω @ V <sub>GS</sub> = 1.8V	640mA
Q2	-20V	0.7Ω @ V <sub>GS</sub> = -4.5V	-640mA
		0.9Ω @ V <sub>GS</sub> = -2.5V	-580mA
		1.3Ω @ V <sub>GS</sub> = -1.8V	-465mA

## Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

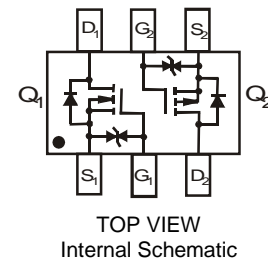
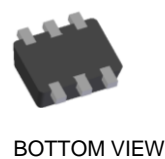
- Switches

## Features

- Low On-Resistance
- Low Gate Threshold Voltage V<sub>GS(th)</sub> <1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- Ultra-Small Surface Mount Package
- ESD Protected Gate to 2.5kV HBM**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**
- PPAP Capable (Note 4)**

## Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (Approximate)

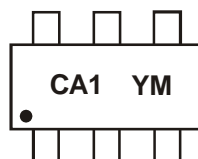


## Ordering Information (Note 5)

Part Number	Case	Packaging
DMG1016VQ-7	SOT-563	3,000/Tape & Reel
DMG1016VQ-13	SOT-563	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  - See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_compliance\\_definitions/](http://www.diodes.com/quality/product_compliance_definitions/).
  - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



CA1 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: W = 2009)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020
Code	W	X	Y	Z	A	B	C	D	E	F	G	H
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (Q1 N-Channel) (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 6$	V
Drain Current (Note 6)	$I_D$	$T_A = +25^\circ\text{C}$	870
		$T_A = +85^\circ\text{C}$	630

**Maximum Ratings** (Q2 P-Channel) (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 6$	V
Drain Current (Note 6)	$I_D$	$T_A = +25^\circ\text{C}$	-640
		$T_A = +85^\circ\text{C}$	-460

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	$P_D$	530	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	235	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (Q1 N-Channel) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	100	nA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	± 1.0	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	—	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	0.3	0.4	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 600mA
		—	0.4	0.5		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 500mA
		—	0.5	0.7		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 350mA
Forward Transfer Admittance	Y <sub>fs</sub>	—	1.4	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 400mA
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 150mA
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	60.67	—	pF	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	9.68	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	5.37	—	pF	
Total Gate Charge	Q <sub>g</sub>	—	736.6	—	pC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Source Charge	Q <sub>gs</sub>	—	93.6	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	116.6	—		
Turn-On Delay Time	t <sub>d(on)</sub>	—	5.1	—	nS	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V, R <sub>L</sub> = 47Ω, R <sub>G</sub> = 10Ω, I <sub>D</sub> = 200mA
Turn-On Rise Time	t <sub>r</sub>	—	7.4	—		
Turn-Off Delay Time	t <sub>d(off)</sub>	—	26.7	—		
Turn-Off Fall Time	t <sub>f</sub>	—	12.3	—		

**Electrical Characteristics** (Q2 P-Channel) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-100	nA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	± 2.0	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	—	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	0.5	0.7	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -430mA
		—	0.7	0.9		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -300mA
		—	1.0	1.3		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -150mA
Forward Transfer Admittance	Y <sub>fs</sub>	—	-0.9	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = -250mA
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	—	-0.8	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -150mA
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	59.76	—	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	12.07	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	6.36	—	pF	
Total Gate Charge	Q <sub>g</sub>	—	622.4	—	pC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -250mA
Gate-Source Charge	Q <sub>gs</sub>	—	100.3	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	132.2	—		
Turn-On Delay Time	t <sub>d(on)</sub>	—	5.1	—	nS	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>L</sub> = 47Ω, R <sub>G</sub> = 10Ω, I <sub>D</sub> = -200mA
Turn-On Rise Time	t <sub>r</sub>	—	8.1	—		
Turn-Off Delay Time	t <sub>d(off)</sub>	—	28.4	—		
Turn-Off Fall Time	t <sub>f</sub>	—	20.7	—		

- Notes: 6. Device mounted on FR-4 PCB.  
7. Short duration pulse test used to minimize self-heating effect.

**Typical Characteristics** (Q1 N-Channel)

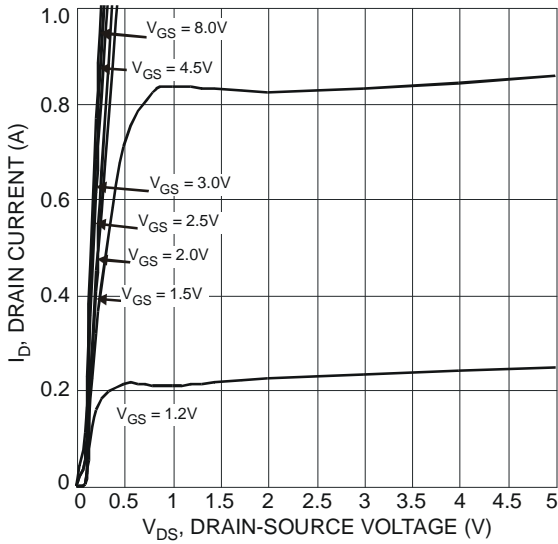


Fig. 1 Typical Output Characteristic

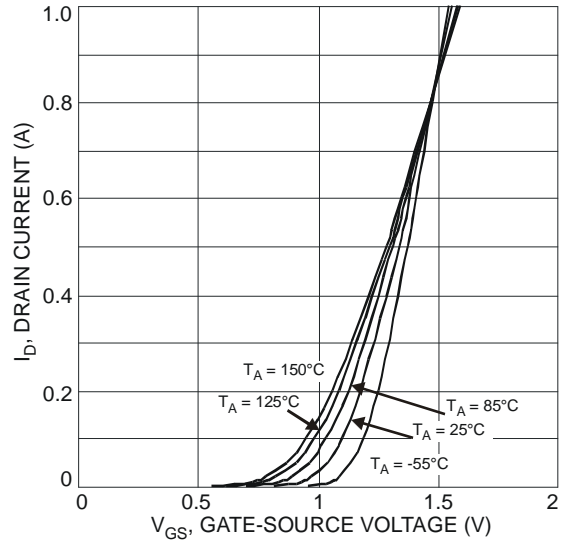


Fig. 2 Typical Transfer Characteristic

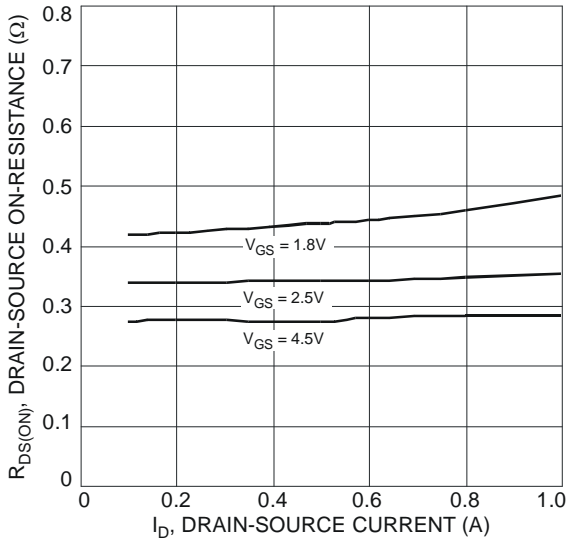


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

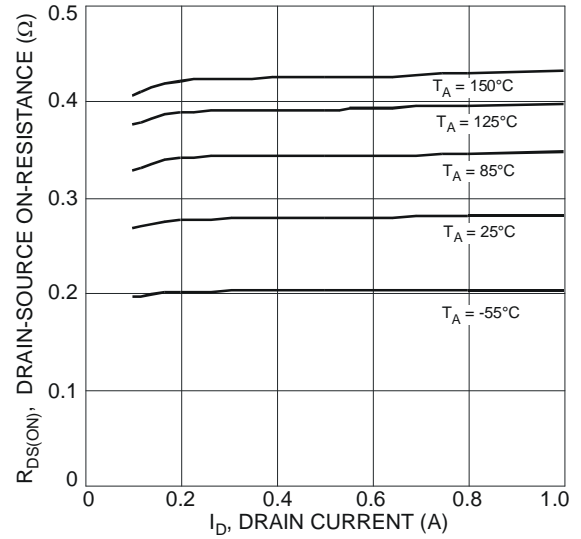


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

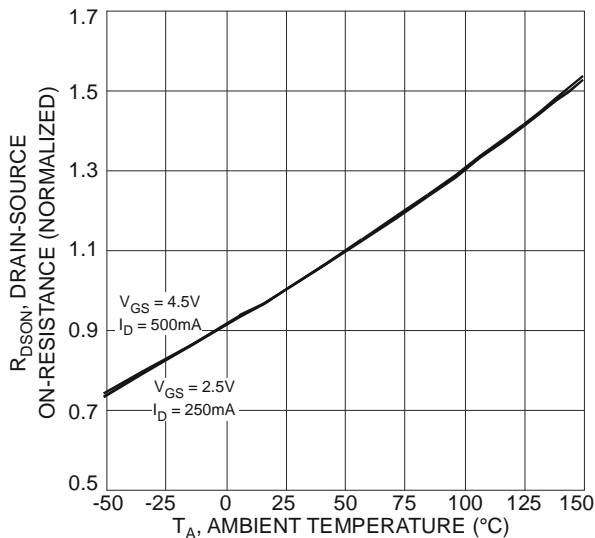


Fig. 5 On-Resistance Variation with Temperature

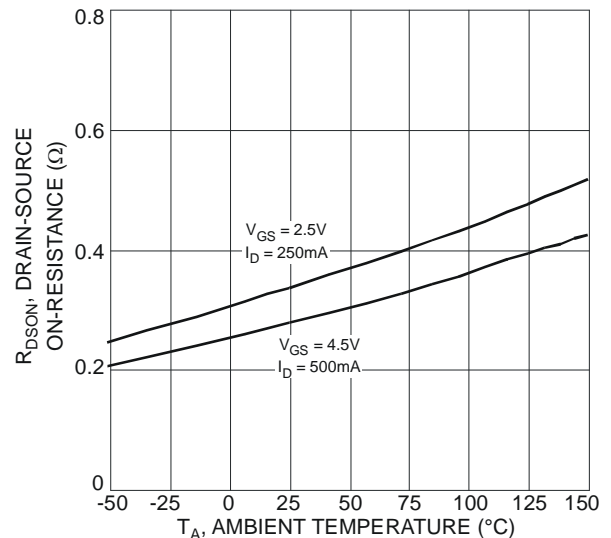


Fig. 6 On-Resistance Variation with Temperature

**Typical Characteristics (Q1 N-Channel) (Continued)**

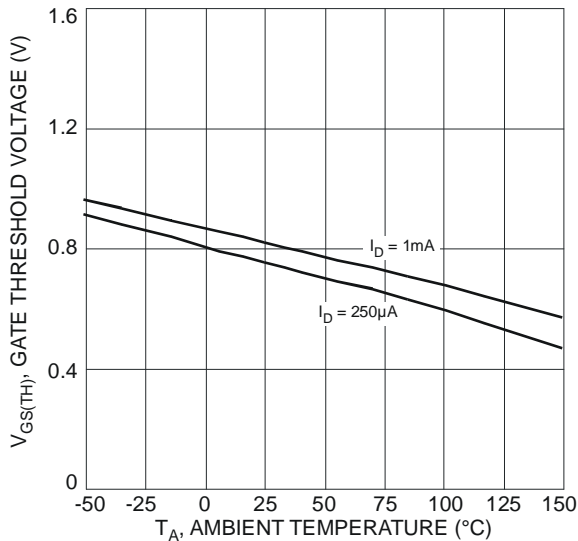


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

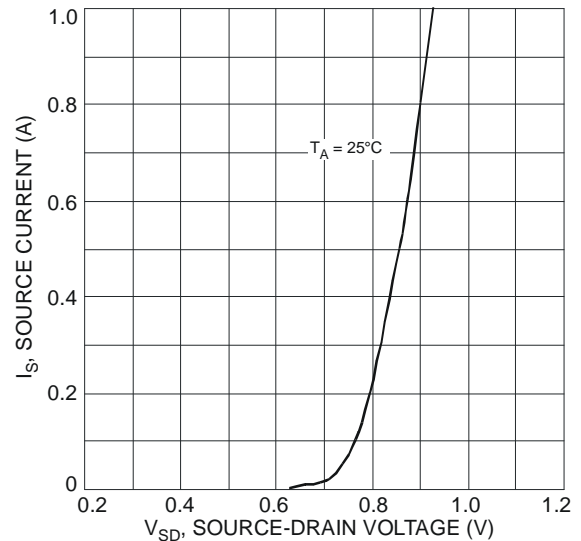


Fig. 8 Diode Forward Voltage vs. Current

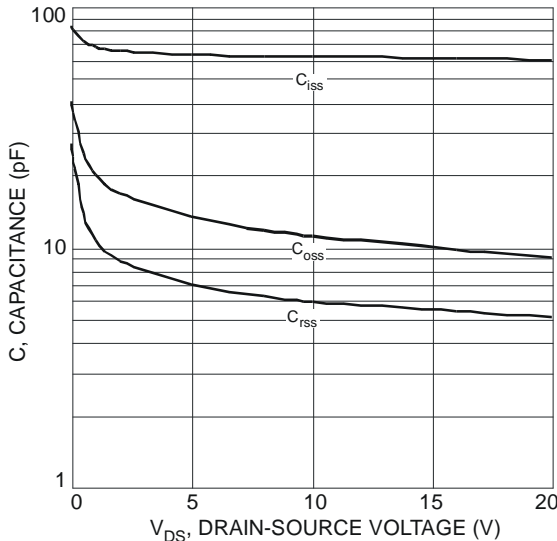


Fig. 9 Typical Total Capacitance

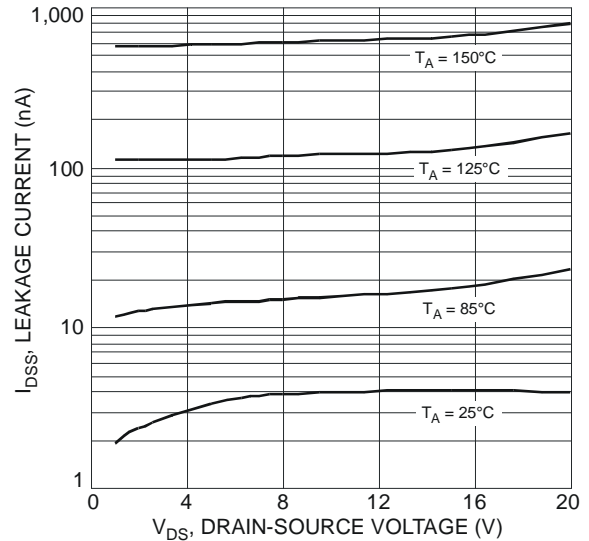


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

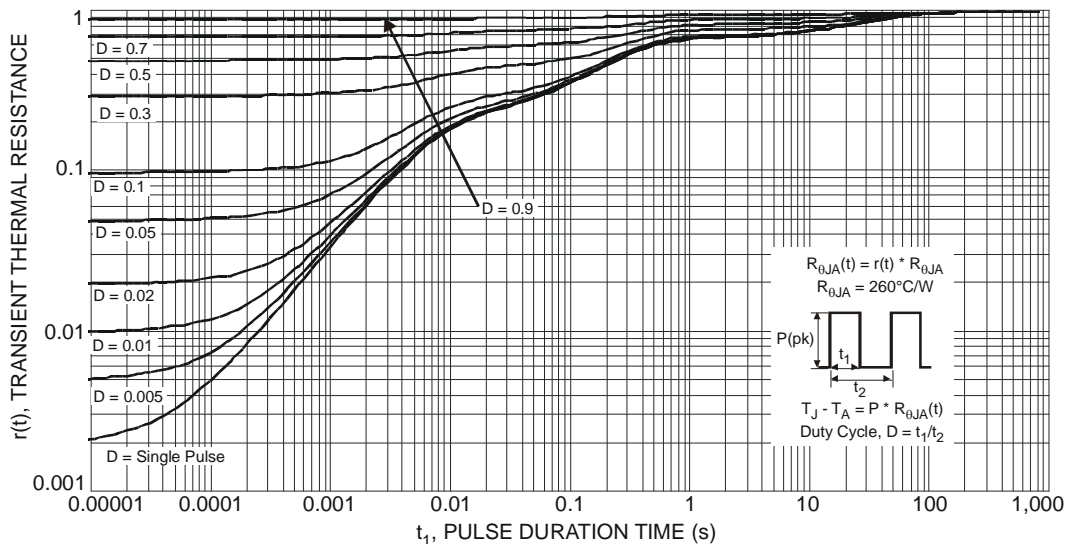


Fig. 11 Transient Thermal Response

**Typical Characteristics (Q2 P-Channel)**

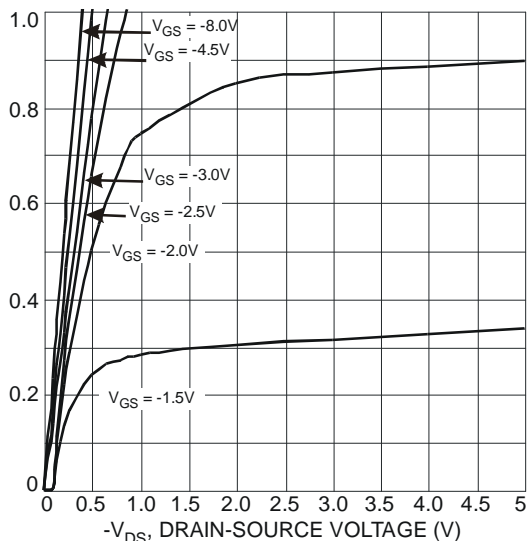


Fig. 12 Typical Output Characteristic

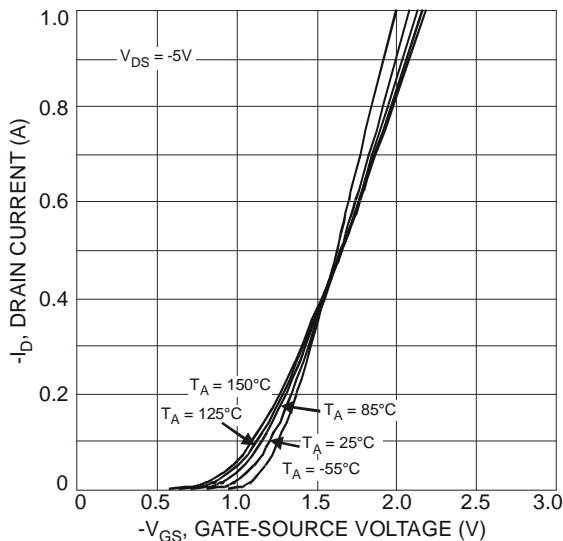


Fig. 13 Typical Transfer Characteristic

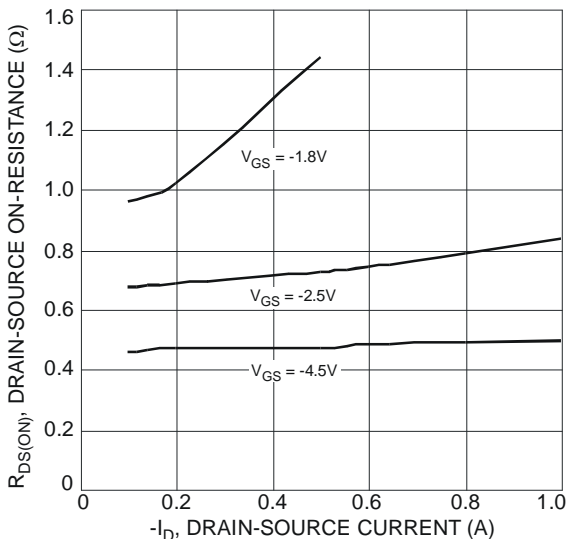


Fig. 14 Typical On-Resistance vs. Drain Current and Gate Voltage

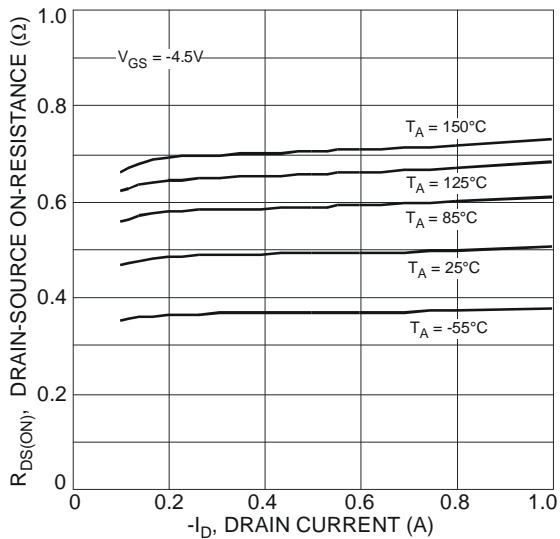


Fig. 15 Typical On-Resistance vs. Drain Current and Temperature

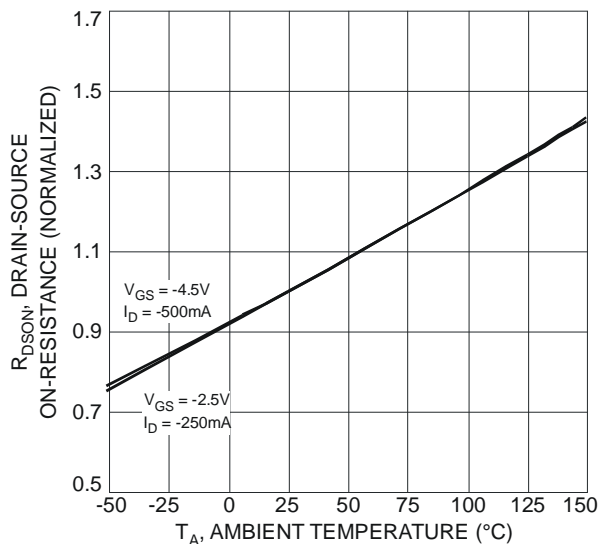


Fig. 16 On-Resistance Variation with Temperature

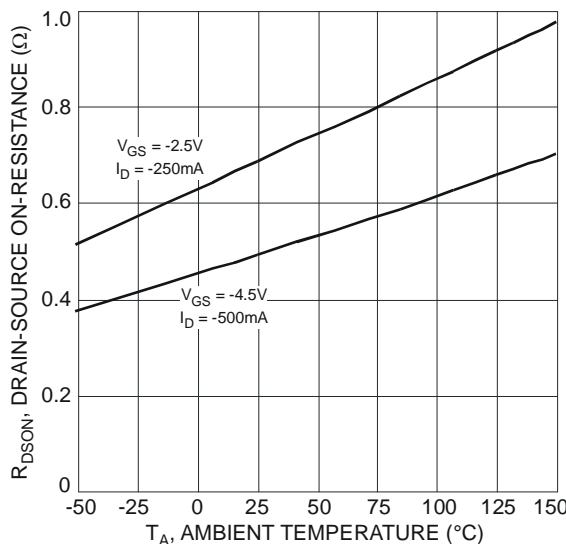


Fig. 17 On-Resistance Variation with Temperature

**Typical Characteristics (Q2 P-Channel) (Continued)**

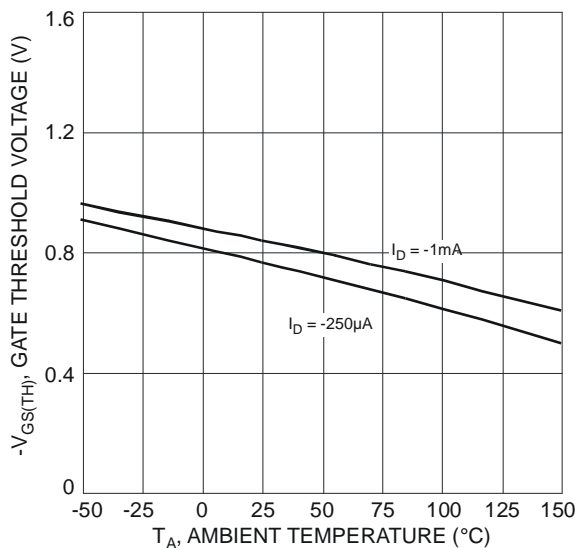


Fig. 18 Gate Threshold Variation vs. Ambient Temperature

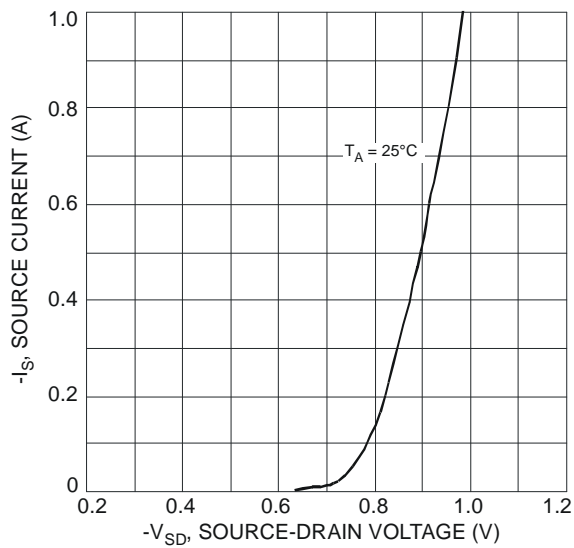


Fig. 19 Diode Forward Voltage vs. Current

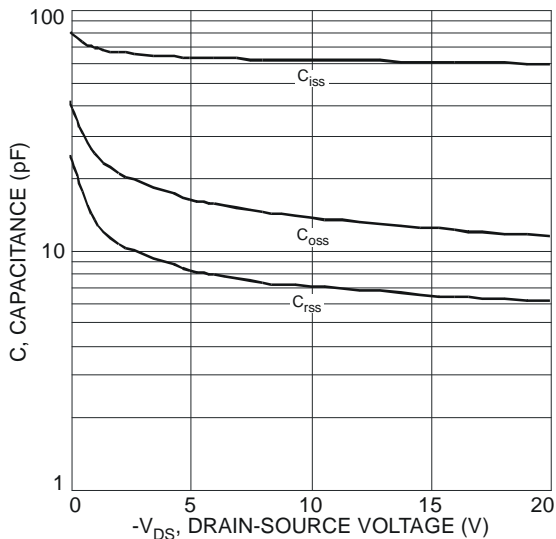


Fig. 20 Typical Total Capacitance

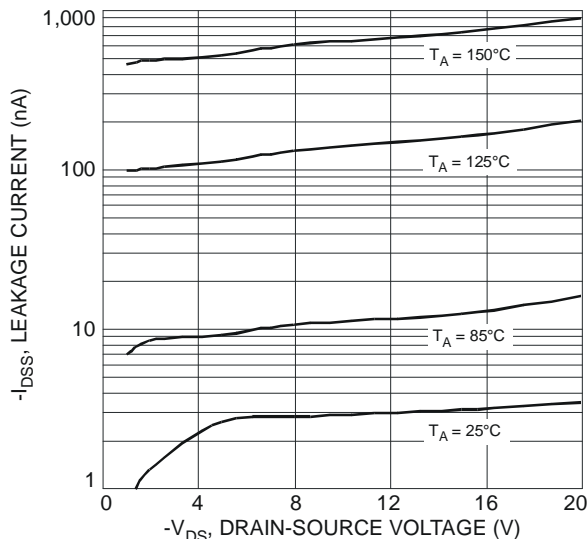


Fig. 21 Typical Leakage Current vs. Drain-Source Voltage

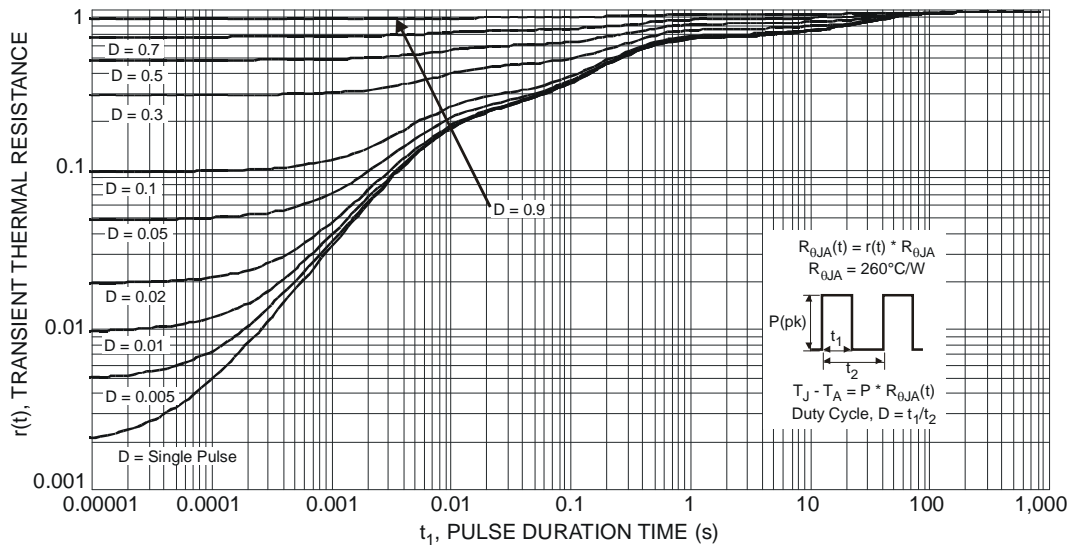
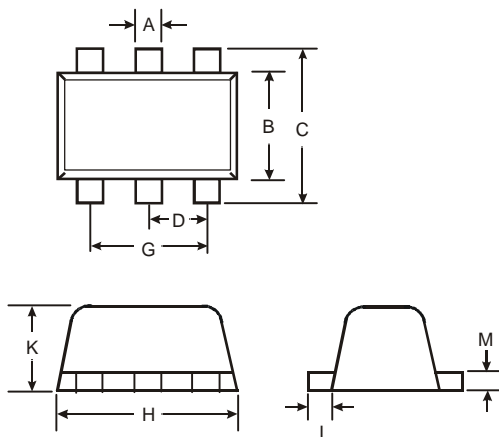


Fig. 22 Transient Thermal Response

**Package Outline Dimensions**

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

**SOT-563**

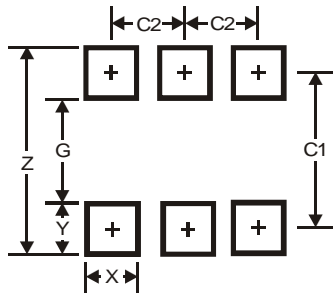


SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

**SOT-563**



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5



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- Консультации по применению компонента;
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- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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